TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX162244FT

LOW-VOLTAGE 16-BIT BUS BUFFER WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

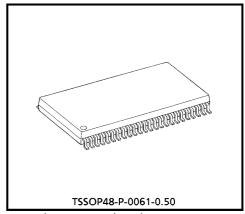
The TC74VCX162244FT is a high performance CMOS 16-bit BUS BUFFER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This device is non-inverting 3 – state buffer having four active-low output enables. It can be used as four 4-bit buffers two 8-bit buffers or one 16-bit buffer. When the \overline{OE} input is high, the outputs are in a high impedance state. This device is designed to be used with 3 – state memory address drivers, etc.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.25 g (Typ.)

FEATURES

• 26- Ω Series Resistors on Outputs.

Low Voltage Operation : V_{CC} = 1.8~3.6 V

• High Speed Operation : $t_{pd} = 3.3 \text{ ns (max)}$ at $V_{CC} = 3.0 \sim 3.6 \text{ V}$

: $t_{pd} = 3.8 \text{ ns (max) at V}_{CC} = 2.3 \sim 2.7 \text{ V}$

: $t_{pd} = 5.7 \text{ ns (max) at V}_{CC} = 1.8 \text{ V}$

• 3.6 V Tolerant inputs and outputs.

• Output Current : $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)}$ at $V_{CC} = 3.0 \text{ V}$

: $I_{OH}/I_{OL} = \pm 8 \text{ mA}$ (min) at $V_{CC} = 2.3 \text{ V}$

: $I_{OH}/I_{OL} = \pm 4 \text{ mA (min)}$ at $V_{CC} = 1.8 \text{ V}$

Latch-up Performance : ±300 mA

■ ESD Performance : Human Body Model > ±2000 V

: Machine Model > ±200 V

Package : TSSOP

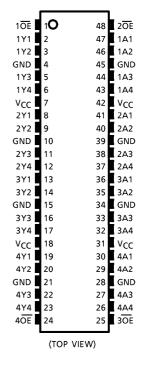
(Thin Shrink Small Outline Package)

Power Down Protection is provided on all inputs and outputs.

Supports live insertion / withdrawal (Note 1)

(Note 1): To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

PIN CONNECTION



980910EBA2

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TRUTH TABLE

INP	UTS	OUTPUTS
1 OE	1A1-1A4	1Y1-1Y4
L	L	L
L	H	Н
Н	Х	Z

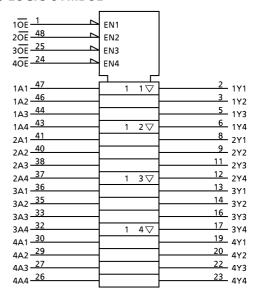
INP	UTS	OUTPUTS
2OE	1A1-2A4	2Y1-2Y4
L	L	L
L	Н	Н
Н	Х	Z

INP	UTS	OUTPUTS
3 OE	3A1-3A4	3Y1-3Y4
L	L	L
L	Н	Н
Н	Х	Z

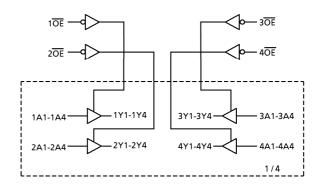
INP	UTS	OUTPUTS
4OE	4A1-4A4	4Y1-4Y4
L	L	L
L	Н	Н
Н	Х	Z

X : Don't Care Z : High impedance

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



980910EBA2'

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MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	Vcc	-0.5~4.6	V
DC Input Voltage	VIN	-0.5~4.6	V
DC Output Voltage	\/ - -	−0.5~4.6 (Note 1)	V
DC Output Voltage	Vout	-0.5~V _{CC} + 0.5 (Note 2)	\ \ \
Input Diode Current	ΙΚ	– 50	mA
Output Diode Current	^I ок	±50 (Note 3)	mA
DC Output Current	IOUT	± 50	mA
Power Dissipation	PD	400	mW
DC V _{CC} / Ground Current Per Supply Pin	ICC/IGND	± 100	mA
Storage Temperature	T _{stg}	-65∼150	°C

(Note 1) : Off-State

(Note 2) : High or Low State. IOUT absolute maximum rating must be observed.

(Note 3) : $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	\/	1.8~3.6	V
Supply Voltage	VCC	1.2~3.6 (Note 4)	V
Input Voltage	V _{IN}	-0.3~3.6	V
Output Voltage	\/ - -	0~3.6 (Note 5)	V
	Vout	0~ V _{CC} (Note 6)	V
		± 12 (Note 7)	
Output Current	IOH/IOL	±8 (Note 8)	mΑ
		±4 (Note 9)	
Operating Temperature	T _{opr}	- 40∼85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns / V

(Note 4) : Data Retention Only (Note 5) : Off-State (Note 6) : High or Low State (Note 7) : $V_{CC} = 3.0 \sim 3.6 \text{ V}$ (Note 8) : $V_{CC} = 2.3 \sim 2.7 \text{ V}$ (Note 9) : $V_{CC} = 1.8 \text{ V}$ (Note 10) : $V_{IN} = 0.8 \sim 2.0 \text{ V}$, $V_{CC} = 3.0 \text{ V}$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

PARA	METER	SYMBOL	TEST	CONDITION	V _{CC} (V)	MIN	MAX	UNIT
Input	"H" Level	VIH				2.0	_	V
Voltage	"L" Level	V _{IL}			2.7~3.6	_	0.8	V
"H" Level		.,	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	1		
	Voн	V _{IN} =	I _{OH} = -6 mA	2.7	2.2		V	
			VIH or VIL	I _{OH} = -8 mA	3.0	2.4	_	
Output	out	I _{OH} = -12 mA	3.0	2.2	_			
Voltage		V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	_	0.2	
	"L" Level			I _{OL} = 6 mA	2.7	_	0.4	v
	L Levei				3.0	_	0.55	·
				I _{OL} = 12 mA	3.0	_	0.8	
Input Leaka	age Current	IN	$V_{IN} = 0 \sim 3$.	6 V	2.7~3.6	_	± 5.0	μ A
3-State Out Off-State C		loz	V _{IN} = V _{IH} · V _{OUT} = 0~	or V _{IL} -3.6 V	2.7~3.6		± 10.0	μΑ
Power Off Current	Leakage	lOFF	V _{IN} , V _{OUT}	= 0~3.6 V	0	1	10.0	μΑ
Quiescent S	Supply	laa	V _{IN} = V _{CC} or GND		2.7~3.6		20.0	
Current		lcc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 V$		2.7~3.6		± 20.0	μ A
Increase In Input	I _{CC} Per	∆ارح	V _{IH} = V _{CC}	- 0.6 V	2.7~3.6	_	750	μΑ

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

PARA	METER	SYMBOL	TEST	TEST CONDITION		MIN	MAX	UNIT	
Input	"H" Level	V_{IH}			2.3~2.7	1.6	_	٧	
Voltage	"L" Level	V _{IL}			2.3~2.7	_	0.7	V	
		.,	I _{OH} = -100 μA	2.3~2.7	V _C C - 0.2	_			
	I II LEVEL I VIJH I	V _{IN} =	$I_{OH} = -4 \text{mA}$	2.3	2.0		V		
Output		VIH or VIL	V_{IH} or V_{IL} $I_{OH} = -6 \text{ mA}$	2.3	1.8				
Voltage				I _{OH} = -8 mA	2.3	1.7	_		
		"L" Level V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	_	0.2		
	"L" Level				IOL = 6 mA	2.3	_	0.4	V
				IOL = 8 mA	2.3	_	0.6		
Input Leak	age Current	ΙΝ	$V_{IN} = 0 \sim 3$.	6 V	2.3~2.7	_	± 5.0	μΑ	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		2.3~2.7		± 10.0	μ A		
Power Off Current	Leakage	lOFF	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μ A	
Quiescent Supply VIN = VCC		or GND	2.3~2.7	_	20.0				
Current		lcc	$V_{CC} \leq (V_{IN})$, V _{OUT}) ≦ 3.6 V	2.3~2.7		± 20.0	μ A	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V \leq V_{CC} < 2.3 V)

PARA	METER	SYMBOL	TEST CONDITION		V _{CC} (V)	MIN	MAX	UNIT
Input	"H" Level	V _{IH}			1.8~2.3	0.7 x V _{CC}		٧
Voltage	"L" Level	V _{IL}			1.8~2.3	_	0.2 x V _C C	٧
Outroot	"H" Level	Voн	V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _C C - 0.2	_	V
Output				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	
Voltage	"L" Level	\/ a .		I _{OL} = 100 μA	1.8	_	0.2	V
	L Level	V _{OL}	V _{IH} or V _{IL}	I _{OL} = 4 mA	1.8	_	0.3	· ' I
Input Leak	age Current	IN	$V_{IN} = 0 \sim 3$.	6 V	1.8	_	± 5.0	μ A
3-State Out Off-State C		loz	V _{IN} = V _{IH} · V _{OUT} = 0~	or V _{IL} ·3.6 V	1.8		± 10.0	μΑ
Power Off Current	Leakage	lOFF	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μΑ
Quiescent Supply		loc	$V_{IN} = V_{CC}$	$V_{IN} = V_{CC}$ or GND		_	20.0	Δ
Current		ICC	$V_{CC} \le V_{IN}$, V _{OUT}) ≦ 3.6 V	1.8		± 20.0	μ A

AC characteristics (Ta = $-40 \sim 85$ °C, Input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CON	DITION _[V _{CC} (V)	MIN	MAX	UNIT
	+			1.8	1.5	5.7	
Propagation Delay Time	t _{pLH} t _{pHL}	(Fig.1, 2)		2.5 ± 0.2	1.0	3.8	ns
-	чрнг		[3	3.3 ± 0.3	8.0	3.3	
3-State Output Enable	t			1.8	1.5	6.7	
	t _{pZL} t _{pZH}	(Fig.1, 3)		2.5 ± 0.2	1.0	5.1	ns
Time			[3	3.3 ± 0.3	8.0	3.8	
3-State Output Disable	4	(Fig.1, 3)		1.8	1.5	5.0	
Time	t _{pLZ}		[2	2.5 ± 0.2	1.0	4.0	ns
Time	t _{pHZ}		[3	3.3 ± 0.3	0.8	3.6	
Output To Output Skew	+			1.8	_	0.5	
	tosLH	(N	ote 11)	2.5 ± 0.2	_	0.5	ns
	^t osHL		[3	3.3 ± 0.3	_	0.5	

For $C_L = 50 \, pF$, add approximately 300 ps to the AC maximum specification.

(Note 11) : Parameter guaranteed by design.
$$(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, \ t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$$

PARAMETER	SYMBOL	TEST CONDITIO	V _{CC} (V)	TYP.	UNIT	
Quiet Quitnut Maximum		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note 12)	1.8	0.15	
Quiet Output Maximum Dynamic VOI	V _{OLP}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	0.25	V
Dynamic vOL		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	0.35	
Quiet Output Minimum	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 12)	1.8	- 0.15	
Dynamic VOI		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	- 0.25	V
Dynamic VOL		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	- 0.35	
Quiet Output Minimum Dynamic V _{OH}		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 12)	1.8	1.55	
	VOHV	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	2.05	V
Dynamic VOH		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	2.65	

(Note 12): Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP.	UNIT
Input Capacitance	CIN		1.8, 2.5, 3.3	6	рF
Output Capacitance	co		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C _{PD}	$f_{IN} = 10 MHz$ (Note 13)	1.8, 2.5, 3.3	20	рF

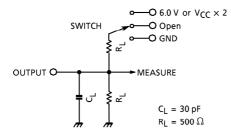
(Note 13): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

ICC (opr.) = CpD · VCC · f_{IN} + I_{CC} / 16 (per bit)

TEST CIRCUIT

Fig.1



PARAMETER	SWITCH		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V @V _{CC} = $3.3 \pm 0.3 \text{ V}$ V _{CC} × 2 @V _{CC} = $2.5 \pm 0.2 \text{ V}$ @V _{CC} = 1.8 V		
t _{pHZ} , t _{pZH}	GND		

AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL}

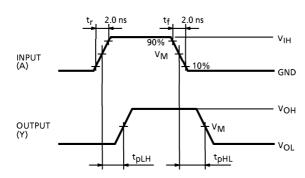
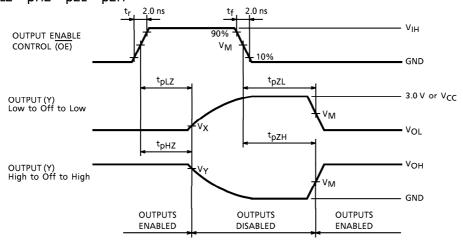


Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

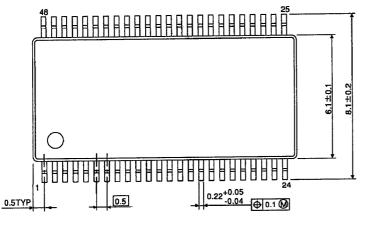


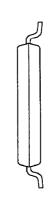
SYMBOL	V _{CC}				
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V		
VIH	2.7 V	Vcc	Vcc		
٧M	1.5 V	V _{CC} /2	V _{CC} /2		
٧x	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V		
VY	V _{OH} – 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V		

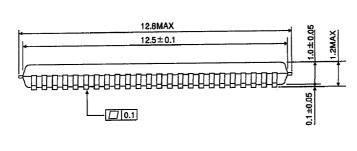
Unit: mm

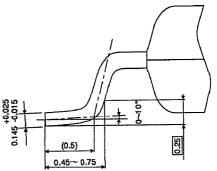
OUTLINE DRAWING

TSSOP48-P-0061-0.50









Weight: 0.25 g (Typ.)

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